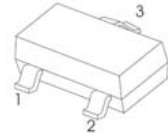


SOT-23 Plastic-Encapsulate MOSFETS
SI2302 N-Channel 20-V(D-S) MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
20V	60mΩ@4.5V	2.0A
	80mΩ@2.5V	

SOT-23


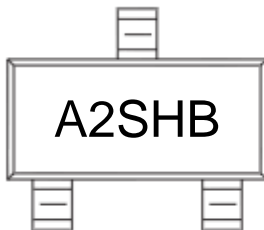
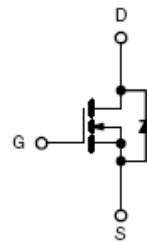
1. GATE
2. SOURCE
3. DRAIN

FEATURE

- TrenchFET Power MOSFET

APPLICATION

- Load Switch for Portable Devices
- DC/DC Converter

MARKING

Equivalent Circuit

Maximum ratings ($T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±12	
Continuous Drain Current	I_D	2.0	A
Continuous Source-Drain Current(Diode Conduction)	I_S	0.6	
Power Dissipation	P_D	0.4	W
Thermal Resistance from Junction to Ambient ($t \leq 5s$)	$R_{\theta JA}$	312.5	$^{\circ}C/W$
Operating Junction	T_J	150	$^{\circ}C$
Storage Temperature	T_{STG}	-55 ~+150	

Notes

- 1) Pulse width limited by maximum junction temperature.
- 2) Surface Mounted on FR4 Board, $t \leq 5$ sec.

The above data are for reference only.



MOSFET ELECTRICAL CHARACTERISTICS

T_a=25 °C unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 10μA	18	20		V
Gate-threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 50μA	0.65	0.95	1.2	
Gate-body leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±8V			±100	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 20V, V _{GS} = 0V			1	μA
Drain-source on-resistance ^a	r _{DS(on)}	V _{GS} = 4.5V, I _D = 2.0A		0.044	0.060	Ω
		V _{GS} = 2.5V, I _D = 1.5A		0.055	0.080	
Forward transconductance ^a	g _{fs}	V _{DS} = 5V, I _D = 3.6A		8		S
Diode forward voltage	V _{SD}	I _S = 0.94A, V _{GS} = 0V		0.76	1.2	V
Dynamic						
Total gate charge	Q _g	V _{DS} = 10V, V _{GS} = 4.5V, I _D = 3.6A		4.0	10	nC
Gate-source charge	Q _{gs}			0.65		
Gate-drain charge	Q _{gd}			1.5		
Input capacitance ^b	C _{iss}	V _{DS} = 10V, V _{GS} = 0V, f = 1MHz		300		pF
Output capacitance ^b	C _{oss}			120		
Reverse transfer capacitance ^b	C _{rss}			80		
Switching^b						
Turn-on delay time	t _{d(on)}	V _{DD} = 10V, R _L = 5.5Ω, I _D ≈ 3.6A, V _{GEN} = 4.5V, R _g = 6Ω		7	15	ns
Rise time	t _r			55	80	
Turn-off delay time	t _{d(off)}			16	60	
Fall time	t _f			10	25	

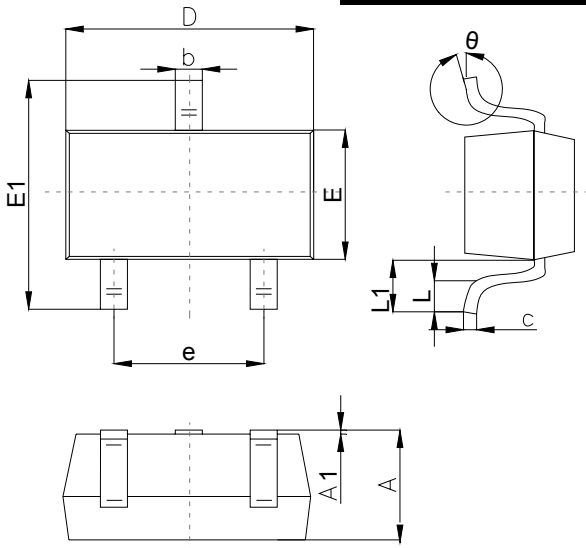
Notes :

- a. Pulse Test : Pulse width ≤ 300μs, duty cycle ≤ 2%.
- b. These parameters have no way to verify.

Figure 3 Power Dissipation

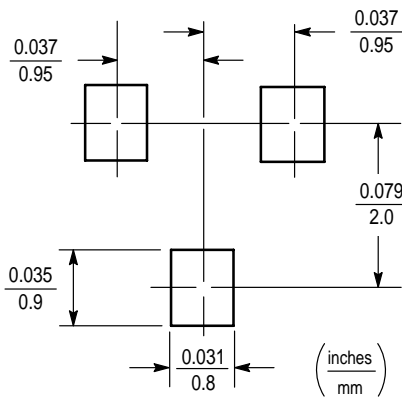
Outline Drawing

SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		
	Min	Typ	Max
A	1.00		1.40
A1			0.10
b	0.35		0.50
c	0.10		0.20
D	2.70	2.90	3.10
E	1.40		1.60
E1	2.4		2.80
e		1.90	
L	0.10		0.30
L1	0.4		
θ	0°		10°

Suggested Pad Layout



- Note:
1. Controlling dimension: in/millimeters.
 2. General tolerance: ±0.05mm.
 3. The pad layout is for reference purposes only.

Important Notice and Disclaimer

Microdiode Electronics (Jiangsu) reserves the right to make changes to this document and its products and specifications at any time without notice. Customers should obtain and confirm the latest product information and specifications before final design, purchase or use.

Microdiode Electronics (Jiangsu) makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Microdiode Electronics (Jiangsu) assume any liability for application assistance or customer product design. Microdiode Electronics (Jiangsu) does not warrant or accept any liability with products which are purchased or used for any unintended or unauthorized application.

No license is granted by implication or otherwise under any intellectual property rights of Microdiode Electronics (Jiangsu).

Microdiode Electronics (Jiangsu) products are not authorized for use as critical components in life support devices or systems without express written approval of Microdiode Electronics (Jiangsu).